

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	46	257/504.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/13 08:33
L2	56	257/545.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/13 08:33
S1	1634	transistor and (fully adj depleted)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/13 08:32
S2	443	transistor and (fully adj depleted) and biased	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 13:45
S3	2	john-mccollum.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 13:45
S4	119	transistor and (fully adj depleted) and (control adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:14
S5	272619	(fully adj depleted adj junctions adj reduce capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:43
S6	0	(fully adj depleted adj junctions adj reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:15
S7	0	(fully adj depleted adj junctions) with (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:16
S8	0	(fully adj depleted adj junctions) same (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:16

S9	0	(fully adj depleted adj junctions) and (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:16
S10	11	(fully adj depleted adj junctions)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:17
S11	1294	transistor and (fully adj depleted) and "257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:03
S12	125	(drift adj region) and (fully adj depleted) and "257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:07
S13	130	(drift adj region) and (fully adj depleted)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:14
S14	252	257/386.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:16
S15	440	257/392.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 05:35
S16	9	pnp with (fully adj depleted)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 17:24
S17	5	parasitic adj surface adj transfer adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 17:26
S18	2	"6573556".pn. and (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 17:52

S19	312	bias\$ near substrate near (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 18:15
S20	258	depletion adj mode adj n adj channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 18:28
S21	2	(full adj depletion adj mode) and bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 18:29
S22	188	(full adj depletion) and bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 18:29
S23	968	257/314.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 05:56
S24	1856	257/315.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:03
S25	344	257/315.ccls. and depletion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 05:57
S26	1886	257/316.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:10
S27	369	257/316.ccls. and depletion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:03
S28	445	257/317.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:12

S29	86	257/317.ccls. and depletion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:11
S30	261	257/318.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:15
S31	291	257/319.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:19
S32	272	257/320.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:23
S33	947	257/321.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:26
S34	208	257/321.ccls. and depletion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:24
S35	233	257/322.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:29
S36	90	257/323.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:31
S37	648	257/324.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:33
S38	146	257/324.ccls. and depletion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:31

S39	149	257/325.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 06:35
S40	234	257/326.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 08:42
S41	27	pnj adj well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 08:59
S42	147	depletion adj well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 09:05
S43	137	depleted adj well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 09:09
S44	264	n adj buried adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 09:31
S45	1689	triple adj well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 09:32
S46	623	(triple adj well) and ((control adj gate) or (floating adj gate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:16
S47	2	"6187635".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 11:29
S48	0	"5487033".pn. and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 12:21

S49	0	"5457652".pn. and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:17
S50	0	"6134150".pn. and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 11:30
S51	0	"6100557".pn. and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 11:30
S52	0	"6169693".pn. and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 11:30
S55	191	(triple adj well) and ((control adj gate) or (floating adj gate)) and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:16
S56	2	"20040026749".pn. and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:32
S57	383	full adj depletion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:10
S58	2	"5617357".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:11
S59	1	"5617357".pn. and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:12
S60	175	(n-well) and (p-well) and (substrate adj bias) and deplet\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:12

S61	0	(fully adj depleted adj junctions adj reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:54
S62	0	(fully adj depleted adj junctions) near (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:44
S63	0	(fully adj depleted adj junctions) with (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:44
S64	0	(fully adj depleted adj junctions) same (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:44
S65	0	(fully adj depleted adj junctions) and (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:50
S66	0	(full adj depleted adj junctions) and (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:50
S67	0	(full adj depletion adj junctions) and (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:50
S68	56	(fully adj depleted) and (reduce adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:50
S69	11	fully adj depleted adj junctions	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:55
S70	1	"6501685".pn. and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:20

S71	11	pnp with npn with (triple adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:36
S72	50	(pnp with npn) with (n adj type adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:51
S73	203	(nnp) with (n adj type adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:57
S74	14	(nnp) and (n adj type adj substrate) and (floating adj gate) and (control adj gate) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:16
S75	0	(nnp) and (p adj type adj buried adj (layer or region)) and (floating adj gate) and (control adj gate) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:18
S76	3	(p adj type adj buried adj (layer or region)) and (floating adj gate) and (control adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:36
S77	1050	(p adj type adj buried adj (layer or region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:24
S78	139	(p near (buried adj (layer or region))) and (n near substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:25
S79	219	(buried adj (layer or region)) and (floating adj gate) and (control adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:36
S80	0	"20040026749".pn. and (p adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:20

S81	0	"20040026749".pn. and (p near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:21
S82	5	interchange adj conductivity adj type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:22
S83	5	interchange adj conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:42
S84	123	(full\$ adj deplet\$) with (n adj (well or type))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 16:30
S85	79	(full\$ adj deplet\$) with ((p adj channel) or pmos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 16:26
S86	174	(full\$ adj deplet\$) same ((p adj channel) or pmos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 16:28
S87	86	(full\$ adj deplet\$) same ((p adj channel) or pmos) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 16:28
S88	131	(full\$ adj deplet\$) with (n adj (well or type or region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 16:30
S89	1050	p adj type adj buried adj (layer or region or portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 06:43
S90	163	(p adj type adj buried adj (layer or region or portion)) and (n adj type adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 07:27

S91	2	"20040065922".pn. and buried	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 07:19
S92	137	(p adj type adj buried adj (layer or region or portion)) and (sti or (isolation and trench))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:08
S93	5	(biased adj buried adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:11
S94	0	(biased adj embedded adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:12
S95	0	(terminal adj (connect\$ or attached) adj embedded adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:12
S96	0	(terminal adj (connect\$ or attached) adj buried adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:15
S97	0	(terminal adj (joined or fastened or fixed) adj buried adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:16
S98	0	(terminal adj (added or affixed) adj buried adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:16
S99	0	(voltage adj (applied) adj embedded adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:19
S10 0	28	(voltage adj applied) with (embedded adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:10

S10 1	175	(voltage adj applied) with (buried adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:28
S10 2	30	(bias adj applied) with (buried adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:28
S10 3	0	("2004/0238913").URPN.	USPAT	OR	ON	2004/12/10 10:24
S10 4	79	(grid) with ((embedded or buried) adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 13:37
S10 5	0	(grid adj formation) with ((embedded or buried) adj (layer or region or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:11
S10 6	52	257/548.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 13:38